

Features

- High Speed Smooth Switching Device for Hard & Soft Switching
- Positive Temperature Coefficient
- High Ruggedness , Temperature Stable
- Maximum junction temperature 175°C
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant (Note 2) ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Applications

- General purpose inverters
- Motor drives
- Uninterruptible power supply

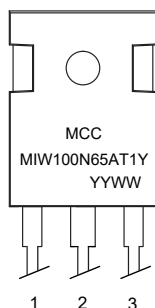
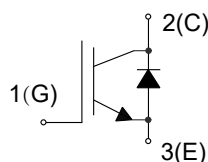
Maximum Ratings

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CE}	650	V
DC Collector Current (Note 3)	I_C	$T_C=25^{\circ}\text{C}$ 160 (Note 4)	A
		$T_C=100^{\circ}\text{C}$ 100	
Pulsed Collector Current, $V_{GE}=15\text{V}$ (Note 5)	$I_{C,pluse}$	400	A
Diode Forward Current (Note 3)	I_F	$T_C=25^{\circ}\text{C}$ 160 (Note 4)	A
		$T_C=100^{\circ}\text{C}$ 100	
Diode Pulsed Current (Note 5)	$I_{F,pluse}$	400	A
Gate-Emitter Voltage	V_{GE}	± 20	V
Transient Gate-Emitter Voltage (Note 6)		± 30	
Power Dissipation	P_D	$T_C=25^{\circ}\text{C}$ 535	W
		$T_C=100^{\circ}\text{C}$ 267.5	

Note:

1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. High Temperature Solder Exemptions Applied, see EU Directive Annex 7a.
3. Limited by T_{Jmax} .
4. Value limited by bondwire.
5. T_p limited by T_{Jmax} .
6. $T_p \leq 10\mu\text{s}$, Duty Cycle < 1%.

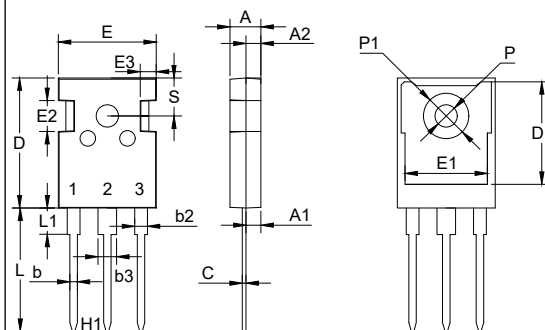
Internal Structure



Device Code: MIW100N65AT1Y
Date Code: YYWW (Year & Week)

Trench and Field Stop IGBT 650V 100A

TO-247AB



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.189	0.205	4.80	5.20	
A1	0.087	0.103	2.21	2.61	
A2	0.073	0.085	1.85	2.15	
b	0.039	0.055	1.00	1.40	
b2	0.075	0.087	1.91	2.21	
C	0.020	0.028	0.50	0.70	
D	0.815	0.839	20.70	21.30	
D1	0.640	0.663	16.25	16.85	
E	0.610	0.634	15.50	16.10	
E1	0.512	0.535	13.00	13.60	
E2	0.189	0.205	4.80	5.20	
E3	0.091	0.106	2.30	2.70	
L	0.772	0.796	19.62	20.22	
L1	-	0.169	-	4.30	
P	0.134	0.150	3.40	3.80	Φ
P1	-	0.287	-	7.30	Φ
S	0.242		6.15		TYP
H1	0.214		5.44		TYP
b3	0.110	0.126	2.80	3.20	

Electrical Characteristics of the IGBT @ $T_J=25^{\circ}\text{C}$ (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
IGBT Static Characteristics						
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=250\mu A$	650			V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=100A, T_J=25^{\circ}\text{C}$	1.10	1.40	1.70	V
		$V_{GE}=15V, I_C=100A, T_J=125^{\circ}\text{C}$		1.50		
		$V_{GE}=15V, I_C=100A, T_J=150^{\circ}\text{C}$		1.60		
G-E Threshold Voltage	$V_{GE(th)}$	$I_C=1mA, V_{CE}=V_{GE}$	4.10	5.10	6.10	V
C-E Leakage Current	I_{CES}	$V_{CE}=650V, V_{GE}=0V, T_J=25^{\circ}\text{C}$			0.25	mA
		$V_{CE}=650V, V_{GE}=0V, T_J=150^{\circ}\text{C}$			3	
G-E Leakage Current	I_{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$			200	nA
Dynamic Characteristics						
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1MHz$		5.13		nF
Reverse Transfer Capacitance	C_{res}			0.05		
Gate Charge	Q_g	$V_{CC}=300V, I_C=100A, V_{GE}=-5V\sim+15V$		0.26		μC
IGBT Switching Characteristics						
Turn-On Delay Time	$t_{d(on)}$	$V_{CC}=300V, I_C=100A,$ $V_{GE}=-5V\sim 15V, R_G=10\Omega, T_J=25^{\circ}\text{C}$ Inductive Load		26		ns
Rise Time	t_r			110		
Turn-Off Delay Time	$t_{d(off)}$			204		
Fall Time	t_f			100		
Turn-On Energy	E_{on}			4.0		mJ
Turn-Off Energy	E_{off}			2.4		
Turn-On Delay Time	$t_{d(on)}$	$V_{CC}=300V, I_C=100A,$ $V_{GE}=-5V\sim 15V, R_G=10\Omega, T_J=125^{\circ}\text{C}$ Inductive Load		27		ns
Rise Time	t_r			97		
Turn-Off Delay Time	$t_{d(off)}$			232		
Fall Time	t_f			138		
Turn-On Energy	E_{on}			4.1		mJ
Turn-Off Energy	E_{off}			3.1		
Turn-On Delay Time	$t_{d(on)}$	$V_{CC}=300V, I_C=100A,$ $V_{GE}=-5V\sim 15V, R_G=10\Omega, T_J=150^{\circ}\text{C}$ Inductive Load		27		ns
Rise Time	t_r			90		
Turn-Off Delay Time	$t_{d(off)}$			240		
Fall Time	t_f			153		
Turn-On Energy	E_{on}			4.2		mJ
Turn-Off Energy	E_{off}			3.4		

Electrical Characteristics of the Diode @ $T_J=25^{\circ}\text{C}$ (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Diode Characteristics						
Diode Forward Voltage	V_F	$V_{GE}=0\text{V}$, $I_F=100\text{A}$, $T_J=25^{\circ}\text{C}$		1.40	1.90	V
		$V_{GE}=0\text{V}$, $I_F=100\text{A}$, $T_J=125^{\circ}\text{C}$		1.35		
		$V_{GE}=0\text{V}$, $I_F=100\text{A}$, $T_J=150^{\circ}\text{C}$		1.30		
Reverse Recovery Current	I_{rr}	$V_R=300\text{V}$, $I_F=100\text{A}$, $di_F/dt=-550\text{A}/\mu\text{s}$, $T_J=25^{\circ}\text{C}$		23		A
Diode Reverse Recovery Time	t_{rr}			116		ns
Reverse Recovery Charge	Q_{rr}			1.8		μC
Reverse Recovery Energy	E_{rec}			0.16		mJ
Reverse Recovery Current	I_{rr}	$V_R=300\text{V}$, $I_F=100\text{A}$, $di_F/dt=-550\text{A}/\mu\text{s}$, $T_J=125^{\circ}\text{C}$		36		A
Diode Reverse Recovery Time	t_{rr}			158		ns
Reverse Recovery Charge	Q_{rr}			4.2		μC
Reverse Recovery Energy	E_{rec}			0.47		mJ
Reverse Recovery Current	I_{rr}	$V_R=300\text{V}$, $I_F=100\text{A}$, $di_F/dt=-550\text{A}/\mu\text{s}$, $T_J=150^{\circ}\text{C}$		41		A
Diode Reverse Recovery Time	t_{rr}			197		ns
Reverse Recovery Charge	Q_{rr}			5.7		μC
Reverse Recovery Energy	E_{rec}			0.61		mJ

Thermal characteristics

Parameter	Symbol	Min	Typ	Max	Units
Operating Junction Temperature Range	T_J	-40		175	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55		150	$^{\circ}\text{C}$
Thermal Resistance from Junction to Case (IGBT)	$R_{th_{J-C}}$			0.28	$^{\circ}\text{C}/\text{W}$
Thermal Resistance from Junction to Case (Diode)	$R_{th_{J-C}}$			0.45	$^{\circ}\text{C}/\text{W}$
Thermal Resistance from Junction to Ambient	$R_{th_{J-A}}$			40	$^{\circ}\text{C}/\text{W}$

Curve Characteristics

Fig. 1 - Typical Output Characteristic($T_j=25^\circ\text{C}$)

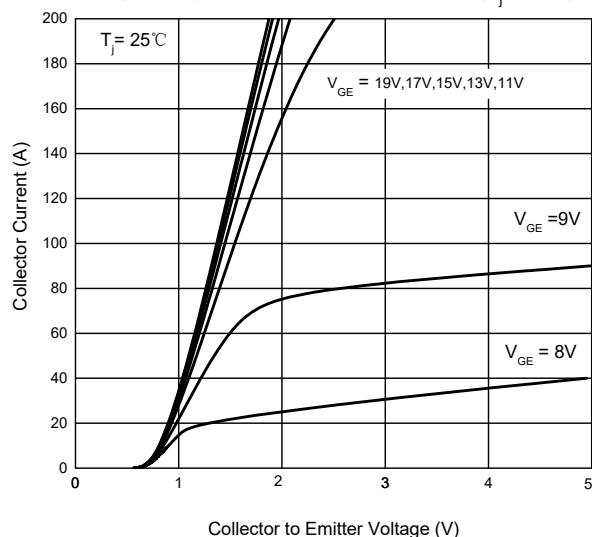


Fig. 2 - Typical Output Characteristic ($T_j=150^\circ\text{C}$)

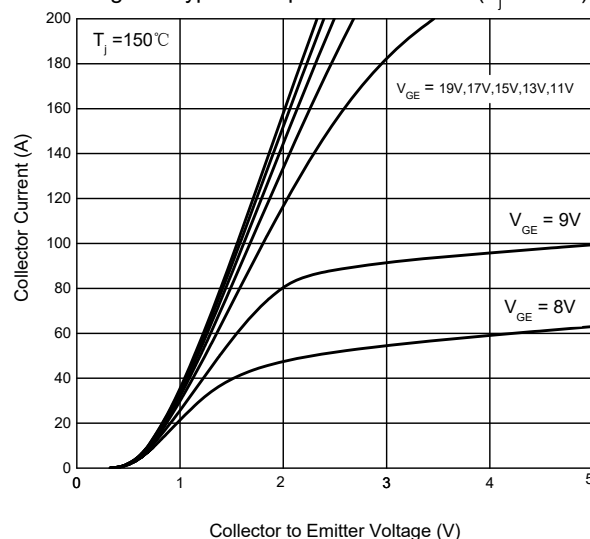


Fig. 3 - Typical Transfer Characteristic

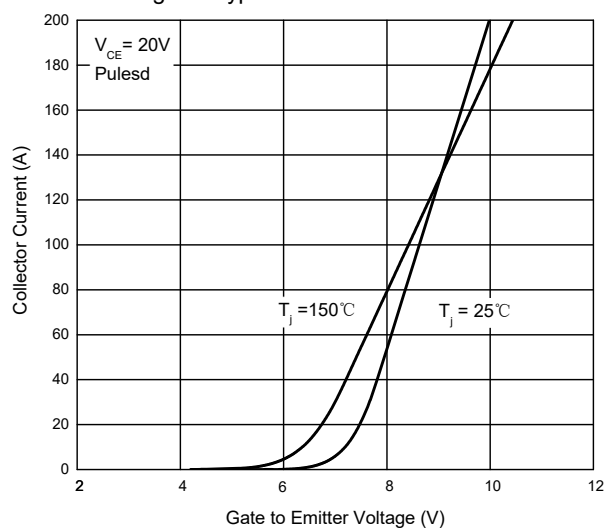


Fig. 4 - Diode Forward Current vs. Forward Voltage

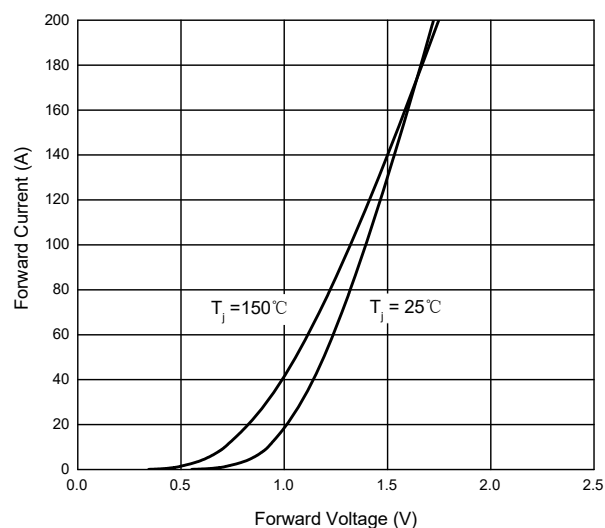


Fig. 5 - Diode VF vs. Junction Temperature

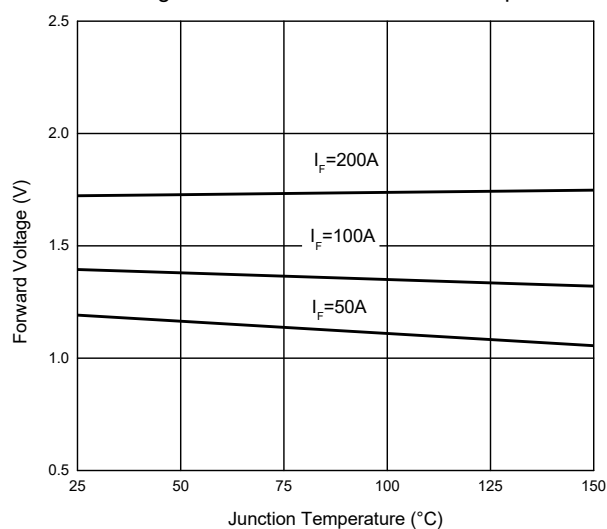
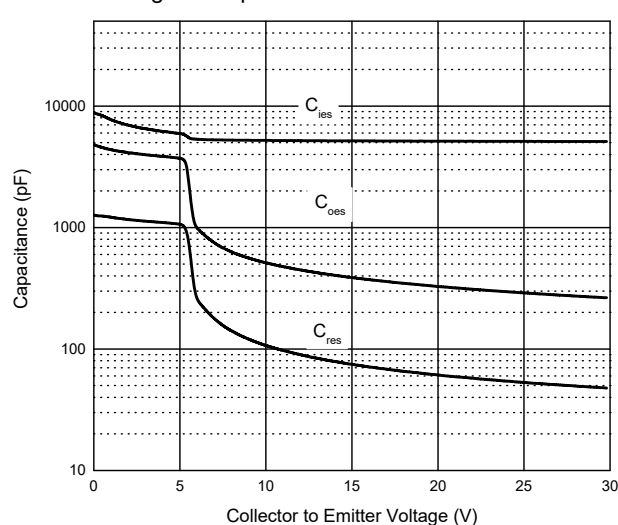


Fig. 6 - Capacitance Characteristics



Curve Characteristics

Fig. 7 - IGBT Switching Loss vs. I_c

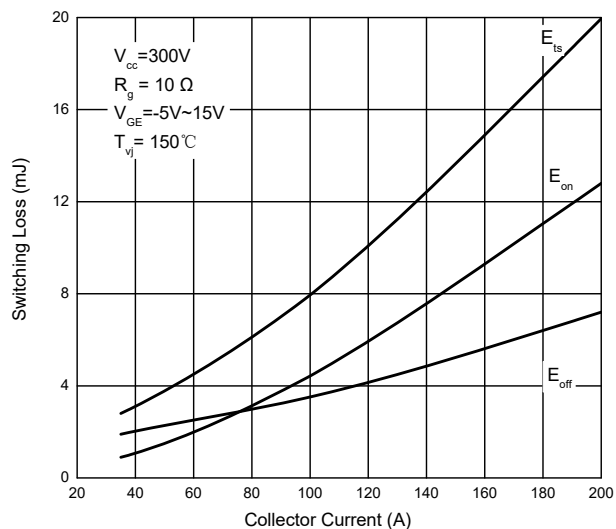


Fig. 8- IGBT Switching Loss vs. R_g

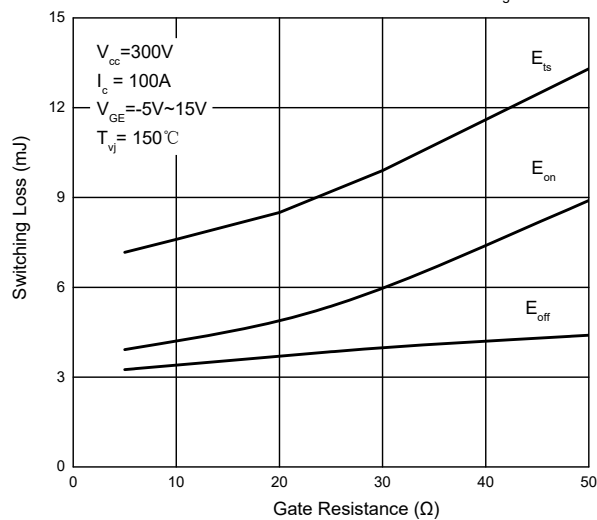


Fig. 9 -IGBT Switching Loss vs. Junction Temperature

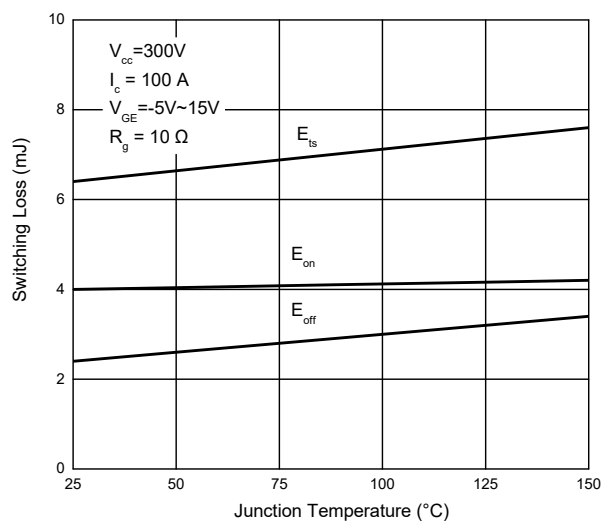


Fig. 10 - Switching Loss vs. V_{CE}

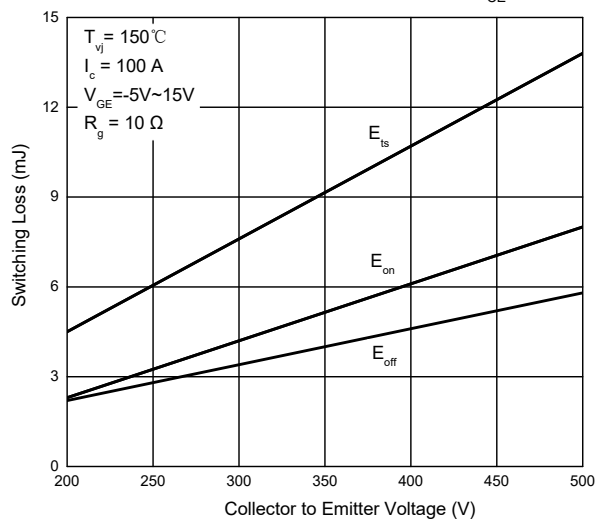


Fig. 11 - $V_{CE(sat)}$ vs. Junction Temperature

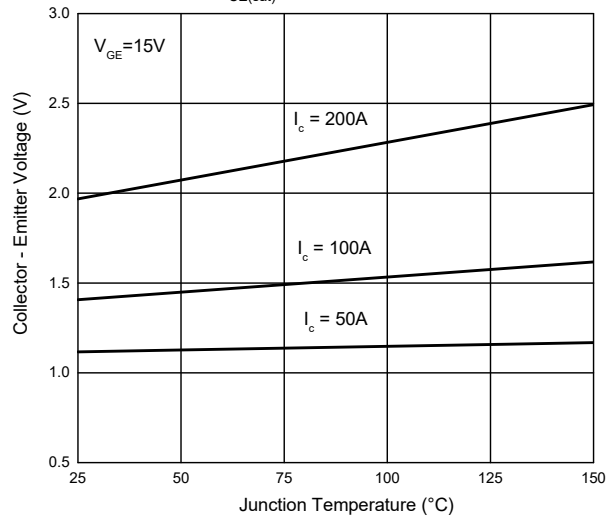
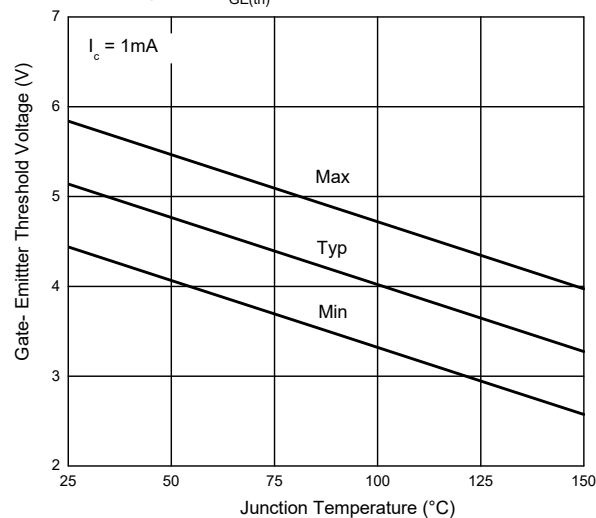


Fig. 12- $V_{GE(th)}$ vs. Junction Temperature



Curve Characteristics

Fig. 13 - Switching Times vs. Collect Current

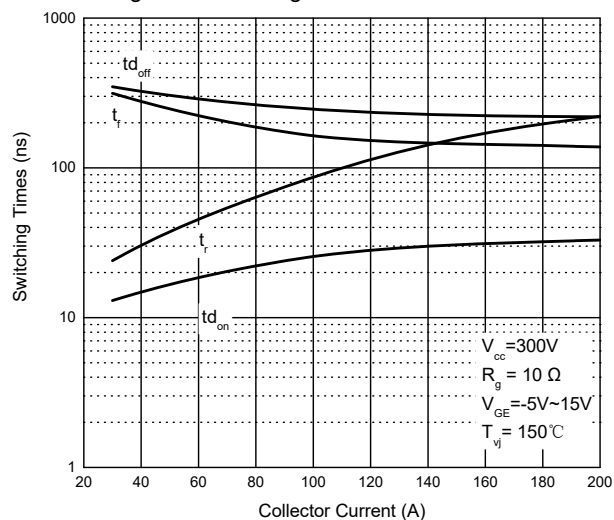


Fig. 14 - Switching Times vs. Gate Resistance

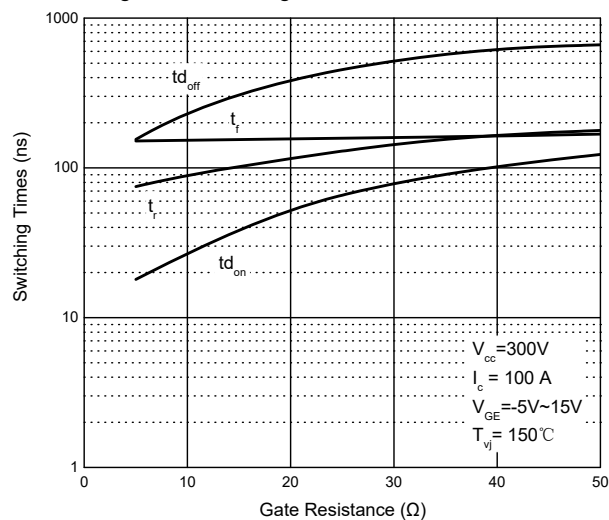


Fig. 15 - IGBT Transient Thermal Impedance

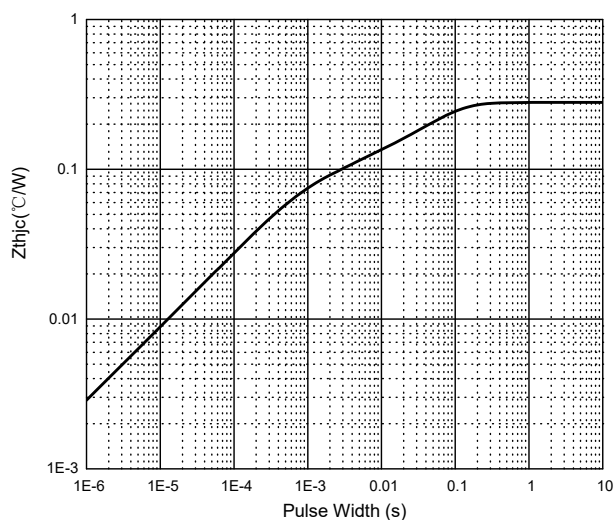


Fig. 16 - Diode Transient Thermal Impedance

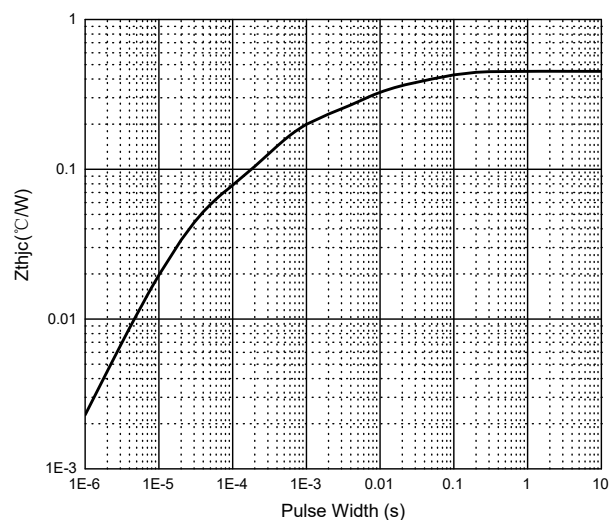


Fig. 17 - Collector Current vs. Case Temperature

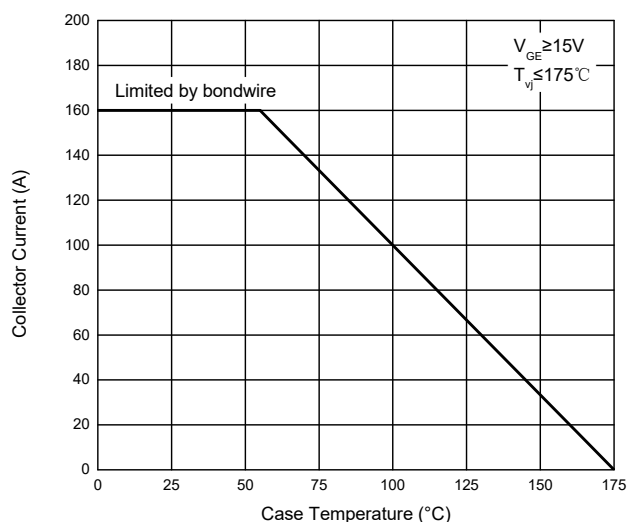
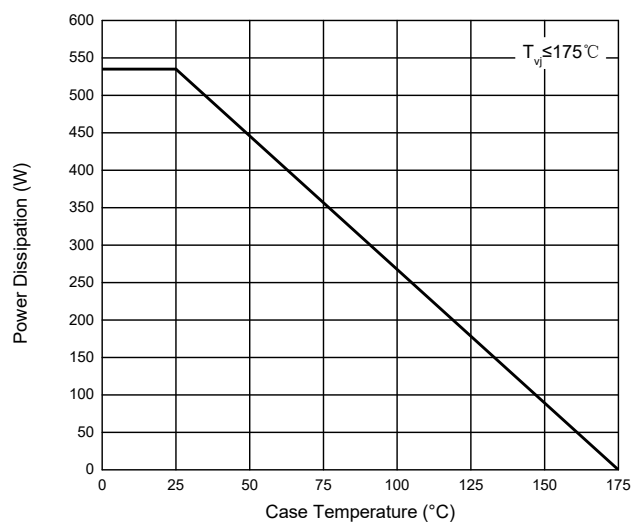
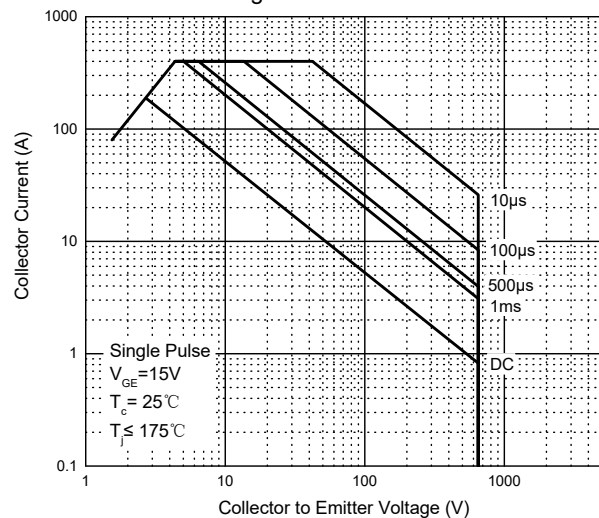


Fig. 18 - Power Derating



Curve Characteristics

Fig. 19 -FBSOA



Ordering Information

Device	Packing
Part Number-BP	Tube: 30pcs/Tube, 1800pcs/Ctn

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